

1030nm, 0.80 NA, aplanoXX Aplan Objective | aplanoXX NA0.8_20_1030

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AdlOptica aplanoXX Aplan Objectives



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1

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A\$13,738⁰⁰

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SPECIFICATIONS

General

aplanoXXNA0.8_20_1030

Model Number:

Type:

Objective	
±0.3	Field of View (°):
Note: Includes aplanoXX objective, mounted protective window (#19-495), and spanner wrench (#19-497)	
Physical & Mechanical Properties	
20	Clear Aperture CA (mm):
44.00	Diameter (mm):
54.10	Length (mm):
Optical Properties	
1030	Design Wavelength DWL (nm):
12.50	Focal Length FL (mm):
0.80	Numerical Aperture NA:
2.5 (1.6 with Protective Window)	Working Distance (mm):
1020 - 1100	Wavelength Range (nm):
100 mJ @ 5ns 300 µJ @ 1ps	Damage Threshold, By Design: ☐
0 - 4	Focusing Depth (mm):
20 (maximum)	Beam Diameter (mm):
100 mJ @ 5ns 300 µJ @ 1ps	Damage Threshold, Pulsed:
Threading & Mounting	
C-Mbunt	Mount:
Regulatory Compliance	
Compliant	RoHS 2015:
View	Certificate of Conformance:
Compliant	Reach 250:

PRODUCT DETAILS

- Aplanatic Optical Design
- High Numerical Aperture for Small Spot Sizes
- Designs for 800 and 1030nm with Focusing Depth Up to 4mm
- AdlOptica foXXus Multi-Focus Objectives Also Available

AdlOptica aplanoXX Aplan Objectives compensate for spherical aberration and coma when focusing into glass, sapphire, silicon carbide, silicon, PMMA, and other transparent materials at depths up to 4mm. These objectives are designed to be used with ultrafast solid-state and fiber lasers and are optimized for 800nm (Ti:sapphire) and 1030nm (Yb:doped). Featuring C-Mbunt threading and an optical design insensitive to misalignment, these objectives are easy to integrate into laser systems. AdlOptica aplanoXX Aplan Objectives are ideal for micromachining glass, 3D nanofabrication, waveguide recording, and selective laser etching. A collar on the objective allows for manual adjustment of focus and a replaceable front window protects from debris during materials processing.

TECHNICAL INFORMATION

